

formed on low-temperature aluminum film 4. A thickness of high-temperature aluminum film is about 200 nm. High-temperature aluminum film 5 includes polycrystalline aluminum and has an average crystal grain size of about 1.5 μm . An opening [107] 7 is formed as a recess in a surface of high-temperature aluminum film 5.

Page 11, please amend the paragraph beginning at line 6 as follows.

Low-temperature aluminum film 21 is formed over recess 6. Low-temperature aluminum film 21 has a thickness of 100 nm and an average grain size of 0.1 μm . A distance between side walls 6a and 6b of recess 6 becomes [small] large as closer to silicon substrate 1. An anti-reflection film 22 having two layers of titanium and titanium nitride is formed on low-temperature aluminum film 21.

IN THE CLAIMS:

9. (Amended) The semiconductor device according to claim 6, wherein each of said first, second and third conductive [layer] layers includes aluminum.

10. (Amended) The semiconductor device according to claim 6, further comprising an insulating layer formed on said semiconductor substrate and a barrier layer formed on said insulating layer, said first conductive layer being formed on said barrier layer.